

## Supplementary Information

### Low-Threshold Room-Temperature Continuous-Wave Optical Lasing of Single-Crystalline Perovskite in a Distributed Reflector Microcavity

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#### 1. Materials and experiments

*Chemical materials and substrates:* Lead bromide powder ( $\text{PbBr}_2$ , 99.99%)  
and methanaminium bromide powder (MABr, 99.99%) were purchased from  
Xi'an Polymer Light Technology Corporation (China); DMF (anhydrous, 99.8%)  
5 from Sigma Aldrich. All the materials were used as received. The double-side  
polished quartz substrates were purchased from Zhongnuo New Material Tech-  
nology Corporation (China); distributed Bragg reflector (DBR) mirrors from  
Fujian CRYSTOCK Corporation (China). All the substrates were cleaned suc-  
cessively with acetone, ethanol and deionized water under sonication for 10 min  
10 and treated by  $\text{O}_2$ -plasma for 10 min.

*Characterization of the thin film:* The PL lifetime was measured by time-  
correlated single-photon counting (TCSPC) setup, by using pump laser source  
(PDL 800-D) and Module and Picosecond Event Timer (PicoHarp 300) from  
PicoQuant. We integrated the data of every sampling dots in a single piece of  
15 complete single-crystalline film as the data of PL lifetime of the film. X-ray  
diffraction (XRD) patterns of the perovskite thin films grown on a quartz sub-

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strate were measured by X-Pert3 powder diffraction system from PANalytical with a Cu tube operated at 40 kV and 40 mA. The surface morphology and cross-sectional images were taken by scanning electron microscope (Helios 600) from FEI Company with 10 kV acceleration voltage. The cross-sectional SEM image of MAPbBr<sub>3</sub> film on DBR substrate (the top DBR has been removed) is shown in Fig S1.

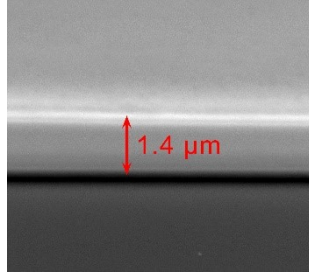


Fig. S1 The cross-sectional SEM image of MAPbBr<sub>3</sub> film on DBR substrate (the top DBR has been removed).

*Optical spectroscopy characterization:* In our handmade PL and laser measurement system, the pump sources were a nanosecond pulsed laser (Nd:YAG laser, frequency tripled, 355 nm, pulse width 8.0 ns, 1.0 kHz) and a continuous-wave semiconductor laser (405 nm). The excitation power was measured by a laser power meter from Thorlab Compony (S120VC). The light spot of the pump laser diode was focused on the center of the perovskite film by a 10x objective lens and the light emission of the devices was collected through a long-pass filter to deduct any residual light from the pump laser. The lasing spectra were recorded on a spectrometer (SR-500i, Andor Technology).

## 2. Coupled oscillator model

As discussed in the main text, to include the effect of exciton-photon, energy ( $E$ ) and wavevector ( $k$ ) have a dispersion relation as follow:

$$E(\omega, k) = \hbar\omega = \hbar ck / \sqrt{\varepsilon(\omega)}$$

The coupled oscillator model of dielectric function was used[1, 2] as:

$$\varepsilon(\omega) = \varepsilon_b \left( 1 + \frac{\omega_L^2 - \omega_T^2}{\omega_T^2 - \omega^2 - i\omega\gamma} \right)$$

Where  $\varepsilon_b = 4.7$  is the background dielectric constant [3],  $\omega_T$  and  $\omega_L$  are the transverse and longitudinal resonance frequencies of exciton and  $\gamma$  is the exciton damping. The parameters  $\hbar\omega_T = 2.303 \text{ eV}$  and  $\hbar\gamma = 59 \text{ meV}$  were taken from reported values [4]. The dispersion curve was fitted by only one parameter,  $\hbar\omega_L$ . With the dielectric function and eigenmode solver simulation of waveguide modes (MODE Solutions, Lumerical), the effective refractive index  $n_{eff}(\lambda)$  was obtained at different wavelengths for the fundamental mode. Then, we have the relations:

$$k_z = \frac{2\pi n_{eff}}{\lambda}$$

$$E = \frac{hc}{\lambda}$$

$k_z$  of the resonant peaks can be placed with integral multiples of  $\pi/h$ , where  $h$  is the thickness of the film. The dispersion curve was fitted as shown in 35 Fig. 2(c) and we obtained the longitudinal-transverse splitting energy  $\Delta E_{LT} = \hbar\omega_L - \hbar\omega_T = 30 \text{ meV}$ .

The mode of the film we calculated concentrate most energy in the gain medium, so we used the volume of the film instead of the effective volume approximately. The exciton-photon coupling strength is expressed as vacuum Rabi splitting energy  $\Omega$ , which was used as [1, 2]:

$$\Omega = \sqrt{\hbar\omega_L^2 - \hbar\omega_T^2} \approx \sqrt{2\Delta E_{LT} \cdot \hbar\omega_T}$$

Then, we obtained vacuum Rabi splitting energy  $\Omega = 372 \text{ meV}$ .

### 3. Rate equation analysis

To better understand the lasing behavior of our devices, we performed a conventional rate equations analysis [5, 6]. The dynamics of the carrier density  $N(t)$  and photon density  $N_p(t)$  that couple into a specific mode can be

represented as follow:

$$\begin{aligned}\frac{dN}{dt} &= \frac{\eta_p P}{\hbar\omega V} - \frac{N}{\tau_{PL}} - v_g g N_p \\ \frac{dN_p}{dt} &= \Gamma v_g (g - g_{th}) N_p + \Gamma \beta \frac{N}{\tau_r}\end{aligned}$$

Where  $\eta_p$  is the fraction of pump power absorbed by the perovskite film which  
 40 we simply chose  $\eta_p = 1$  because of the high absorption coefficient.  $P$  is the  
 pump power and  $V$  is the volume of gain medium, so  $P/V$  is the pump power  
 density times the thickness of gain medium which is  $1.36 \mu m$ .  $\hbar\omega$  is the energy  
 of the pump beam.  $\tau_{PL}$  is the PL lifetime, which is set to be  $426 ns$  from  
 the PL lifetime measurement in Fig. 1(c) and  $\tau_r$  is the spontaneous emission  
 45 lifetime. Here we adopted the value of  $1000 ns$  according to the reported longest  
 PL lifetime [7, 8].  $\Gamma$  is the optical confinement factor which we set  $\Gamma = 1$ ,  
 because the DBR mirrors with high reflectivity had extremely strong optical  
 confinement on the optical mode we cared about.  $v_g$  is the group velocity, and  
 from mode analysis using Lumerical Mode solutions we obtained  $v_g = c/2.29$   
 50 for CW pumped lasing and  $v_g = c/2.285$  for pulsed pumped lasing, where  $c$  is  
 the light velocity in vacuum.  $g_{th}$  is the equivalent threshold gain, and  $\beta$  is the  
 spontaneous emission factor.  $g$  is the gain and a linear relation between gain  
 and carrier density  $N$  is assumed in the active region,  $g(N) = \alpha(N - N_{tr})$ ,  
 where  $\alpha$  is a material constant, and  $N_{tr}$  is the transparency carrier density,  
 55 which is approximated to zero for simplicity [6].

For the CW pumped lasing, all time differential terms are zero. The carrier  
 density is eliminated and the rate equations are reduced to an algebraic equation  
 as follow:

$$\frac{\eta_p P}{\hbar\omega V} \left( \frac{\beta}{\tau_r} + v_g \alpha N_p \right) = v_g g_{th} N_p \left( \frac{1}{\tau_{PL}} + v_g \alpha N_p \right)$$

We fitted the algebraic equation with the data points and obtained the sponta-  
 neous emission factor  $\beta = 0.08$ , as shown in Fig. 4(d).

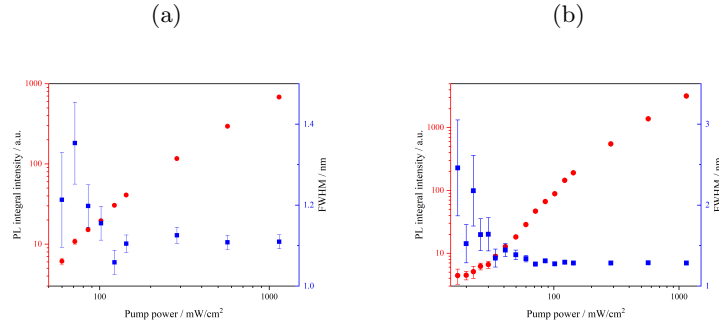


Fig. S2 (a) The intensity and FWHM of 547 nm peak change along with increasing pump fluences in a logarithmic coordinate system. (b) The intensity and FWHM of 591 nm peak change along with increasing pump fluences in a logarithmic coordinate system.

#### 4. Analysis of the side peaks in CW pumping case

The integral intensity and FWHM of the peaks at 547 and 591 nm are shown in Fig. S2. The peak at 547 nm is much weaker and undetectable under the pump fluences below  $50 \text{ mW/cm}^2$ . From the remaining data under higher pump fluences shown in Fig. S2(a), no obvious nonlinear change is observed. The FWHM is 1.1 nm at the highest pump fluence.

On the other hand, the peak at 591 nm can be fitted well by Gaussian curves. A visible S-shaped curve is observed in Fig. S2(b). The nonlinear change of the intensity and the narrowing of linewidth appear simultaneously under the pump fluence of around  $34 \text{ mW/cm}^2$ . This peak is near the edge of the high reflection zone as shown in Fig. 4(b) so that the final FWHM is 1.3 nm, which is larger than the one of the center peak.

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